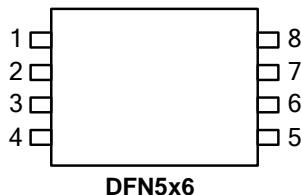


N-Channel Power MOSFET

General Description		Product Summary	
• Very low on-resistance $R_{DS(ON)}$		V_{DS}	100V
• Low Gate Charge		I_D	65A
• Excellent Gate Charge x $R_{DS(ON)}$ Product		$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 14mΩ(Max)
		$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 17mΩ(Max)
Applications		100% DVDS Tested	
• High Frequency Switching and Synchronous Rectification		100% UIS Tested	
		100% R_g Tested	



Part Number	Package Type	Form	Marking
SL65N10Q	DFN5x6	Tape & Reel	SL65N10Q

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current <small>$T_C = 100^\circ C$ ^B</small>	I_D	65	A
		40	
Pulsed Drain Current ^A	I_{DM}	130	A
Avalanche Current ^A	I_{AS}	60	A
Single Pulse Avalanche Energy <small>$L = 0.3mH$ ^A</small>	E_{AS}	180	mJ
Power Dissipation ^C	P_D	89	W
		2.5	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case	R_{eJC}	62	°C/W
Maximum Junction-to-Ambient	R_{eJA}	1.4	

Electrical Characteristics@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=10\text{mA}$	100	-	-	V
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=20\text{A}$	-	-	14	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=20\text{A}$	-	-	17	$\text{m}\Omega$
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\text{\mu A}$	1.2	-	2.4	V
g_{fs}	Forward Transconductance	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=20\text{A}$	-	30	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	uA
I_{GSS}	Gate-Source Leakage	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Q_g	Total Gate Charge	$I_{\text{D}}=20\text{A}$	-	75	-	nC
Q_{gs}	Gate-Source Charge	$V_{\text{DS}}=15\text{V}$	-	15	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{\text{GS}}=4.5\text{V}$	-	20	-	nC
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DS}}=15\text{V}$	-	18	-	ns
t_r	Rise Time	$I_{\text{D}}=1\text{A}$	-	8	-	ns
$t_{\text{d(off)}}$	Turn-off Delay Time	$R_G=3.3\Omega$	-	58	-	ns
t_f	Fall Time	$V_{\text{GS}}=10\text{V}$	-	15	-	ns
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}$	-	4708	-	pF
C_{oss}	Output Capacitance	$V_{\text{DS}}=15\text{V}$	-	326	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	247	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.6	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_{\text{S}}=20\text{A}, V_{\text{GS}}=0\text{V}$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$I_{\text{S}}=20\text{A}, V_{\text{GS}}=0\text{V},$ $dI/dt=100\text{A}/\mu\text{s}$	-	24	-	ns
			-	30	-	nC

Typical Characteristics

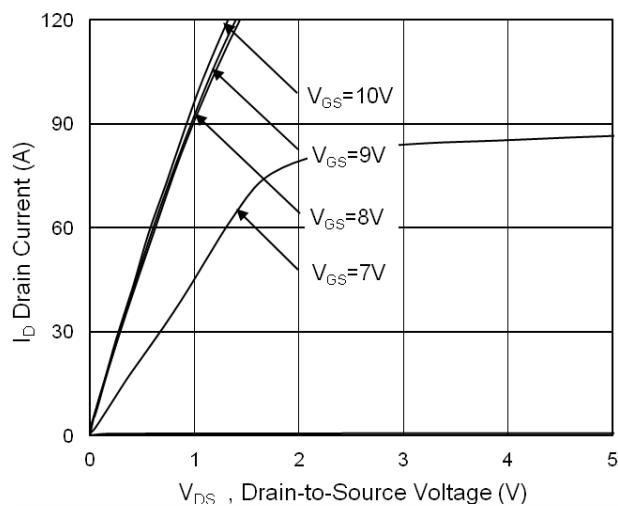


Fig.1 Typical Output Characteristics

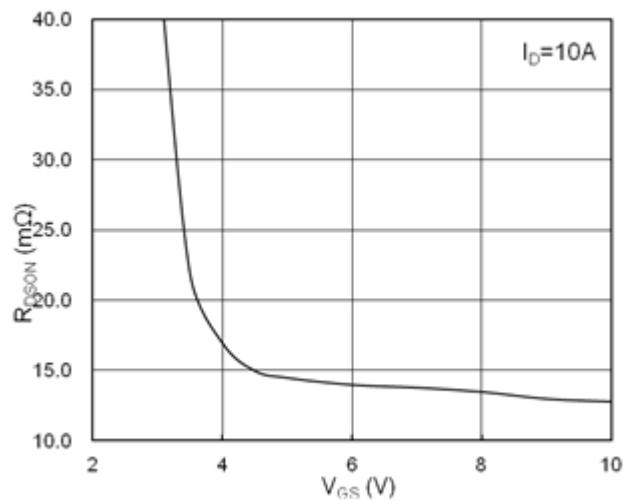


Fig.2 On-Resistance v.s Gate-Source

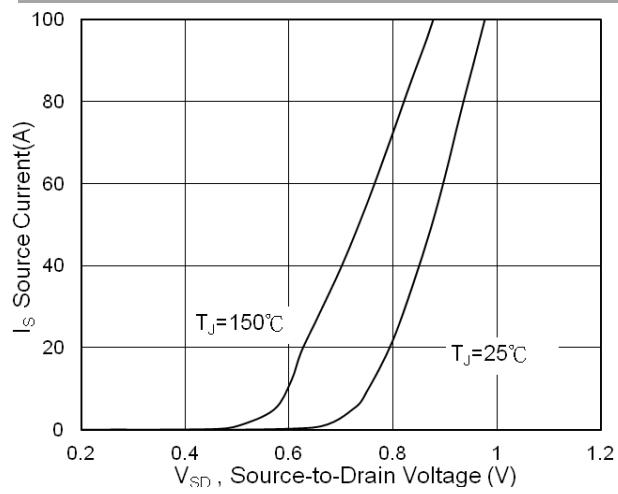


Fig.3 Forward Characteristics of Reverse

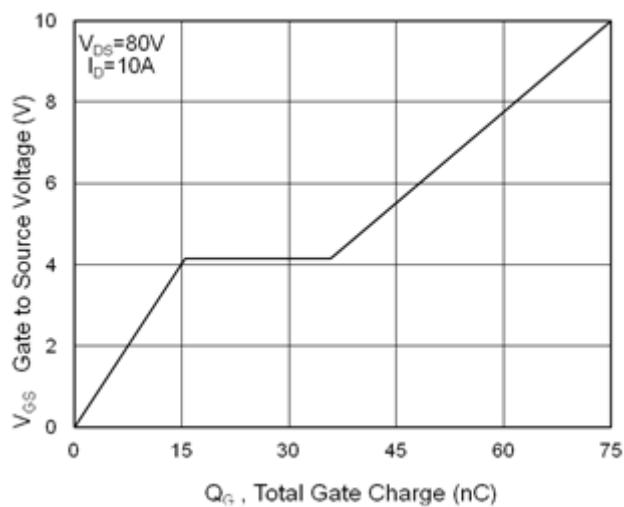


Fig.4 Gate-Charge Characteristics

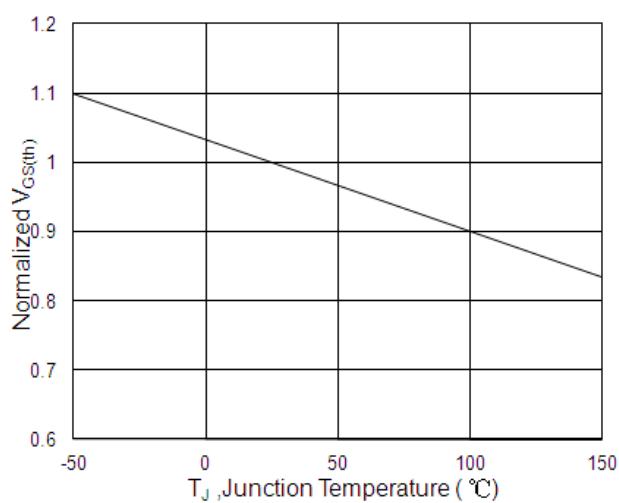


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

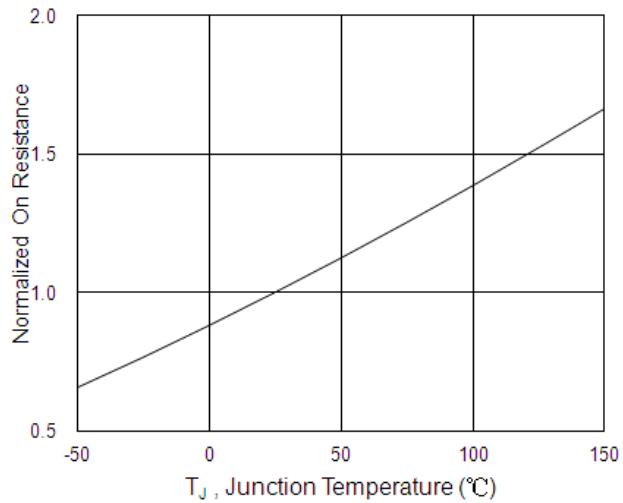


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

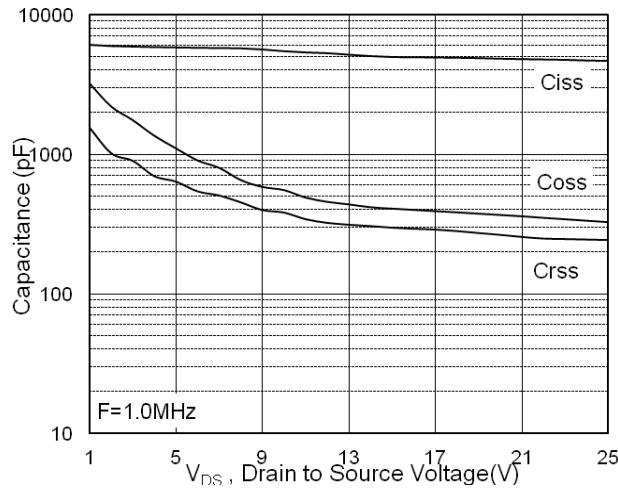


Fig.7 Capacitance

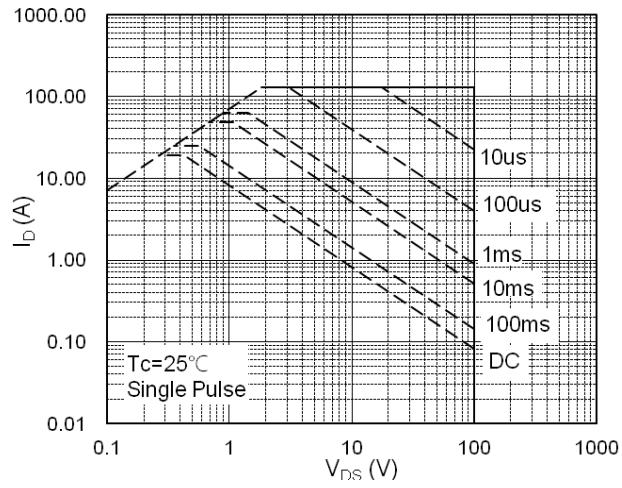


Fig.8 Safe Operating Area

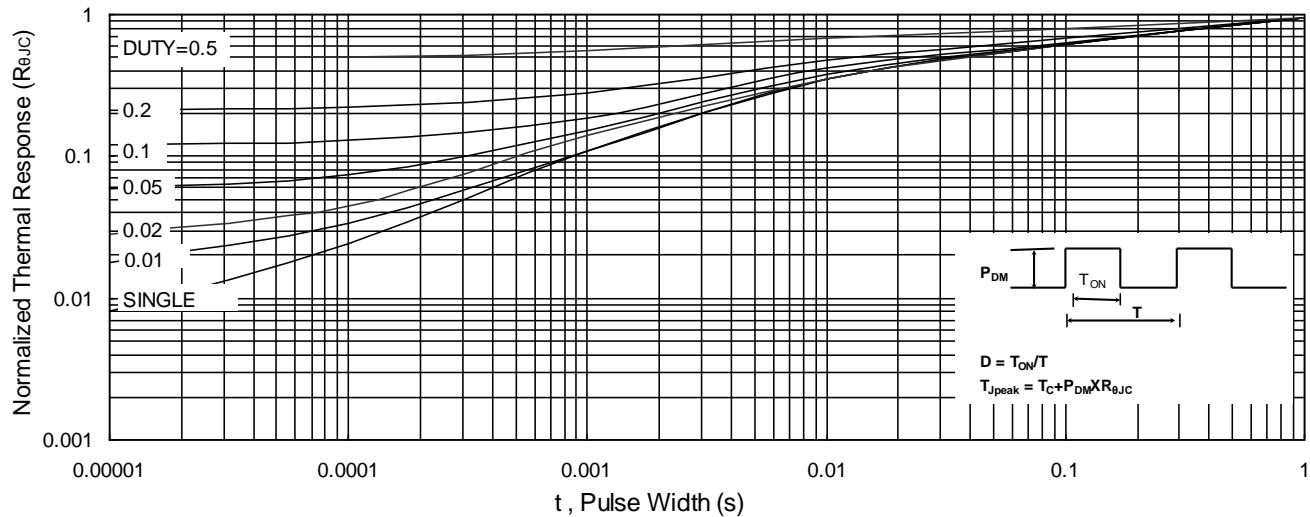


Fig.9 Normalized Maximum Transient Thermal Impedance

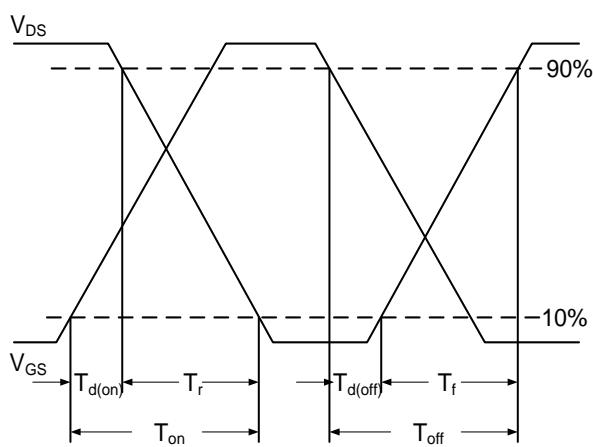


Fig.10 Switching Time Waveform

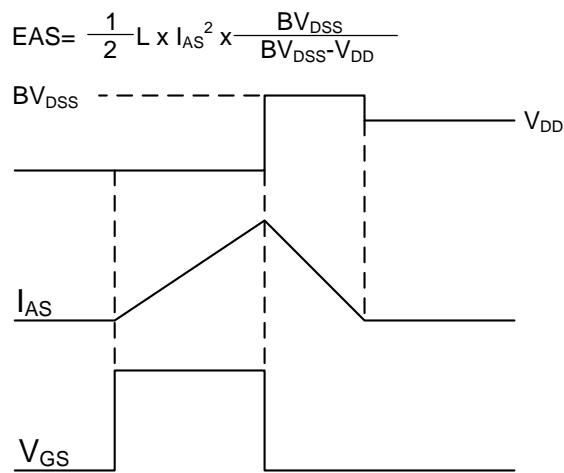
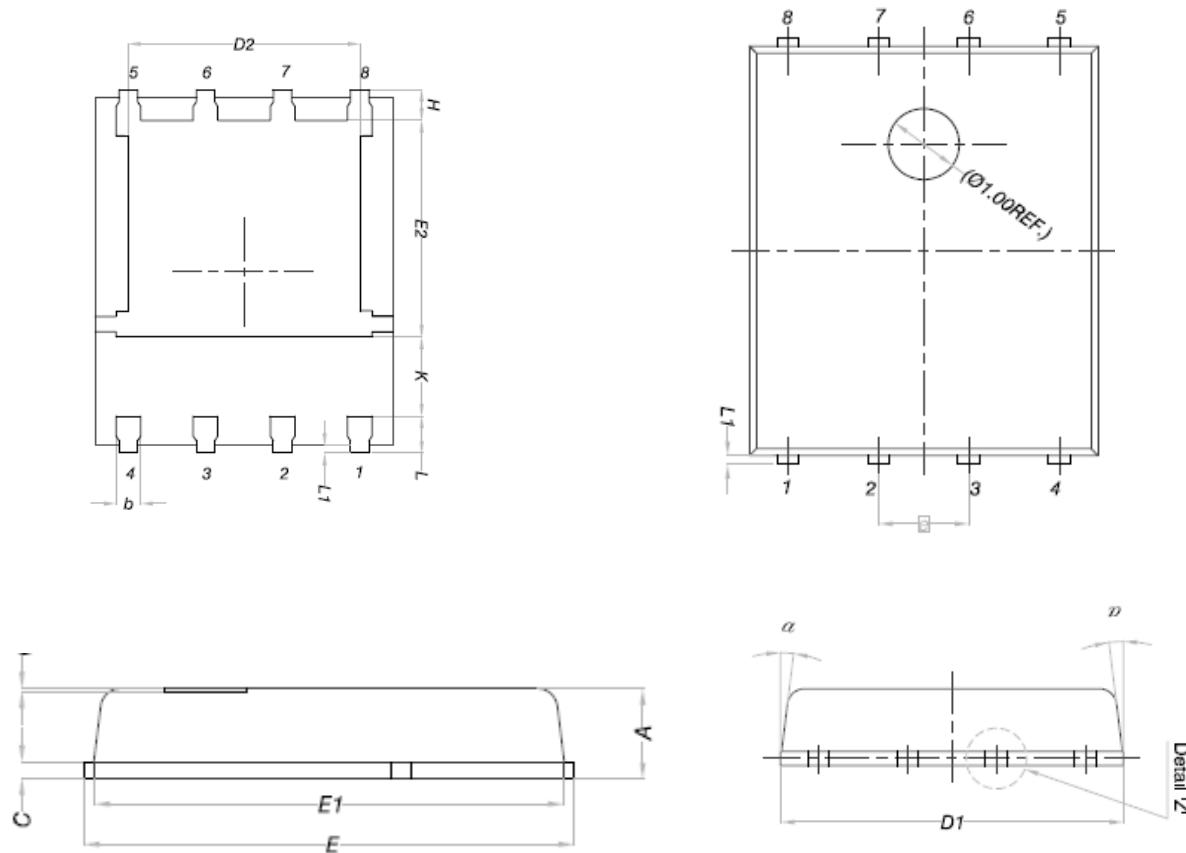


Fig.11 Unclamped Inductive Switching Waveform

DFN5x6



DIM.	MILLIMETERS			DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	0.90	1.00	1.10	E	5.90	6.00	6.10
A1	0	-	0.05	E1	5.70	5.75	5.80
b	0.33	0.41	0.51	E2	3.38	3.58	3.78
C	0.20	0.25	0.30	e	1.27 BSC		
D1	4.80	4.90	5.00	H	0.41	0.51	0.61
D2	3.61	3.81	3.96	K	1.10	-	-
				L	0.51	0.61	0.71
				L1	0.06	0.13	0.20
				α	0°	-	12°

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